

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

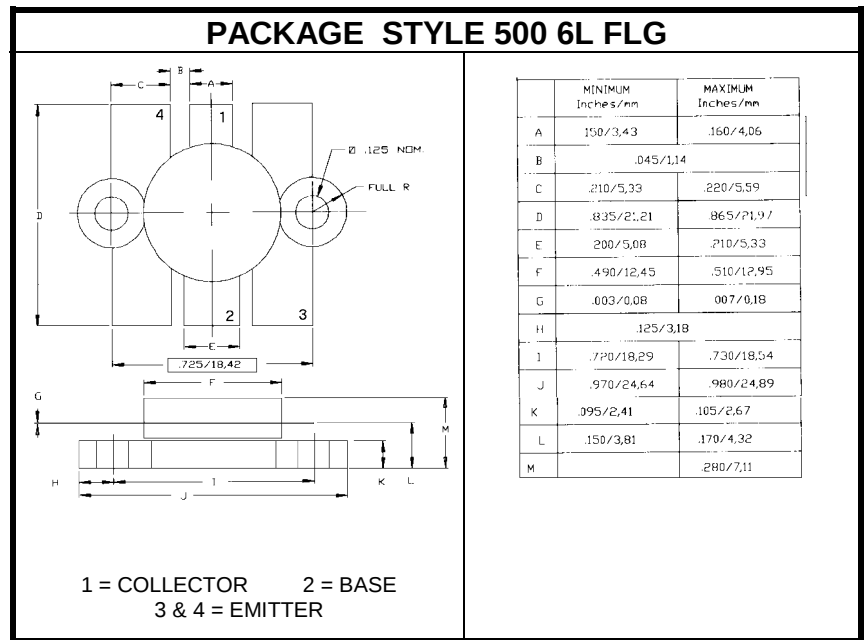
The **ASI TPV385** is Designed for Operation in Band III TV Transposers and Transmitter Amplifiers from 170 to 230 MHz.

FEATURES INCLUDE:

- Gold Metalization
- Emitter Ballast Resistors
- Internal Input Matching
- Common Emitter

MAXIMUM RATINGS

I_C	10 A (CONT)
V_{CB}	65 V
V_{CE}	35 V
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	1.5 °C/W



CHARACTERISTICS $T_C = 25\text{ }^{\circ}\text{C}$

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV _{CEO}	I _C = 50 mA			35			V
BV _{CER}	I _C = 50 mA	R _{BE} = 10 Ω		60			V
BV _{CBO}	I _C = 50 mA			65			V
BV _{EBO}	I _E = 10 mA			4.0			V
h _{FE}	V _{CE} = 5.0 V	I _C = 1.0 A		20		100	---
C _{ob}	V _{CB} = 30 V						